Giorgia Franzo

List of Publications by Year
in descending order

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171 papers	9,389 citations	66315 42 h-index	38368 95 g-index
172 all docs	172 docs citations	172 times ranked	4555 citing authors

#	Article	IF	Citations
1	Optical gain in silicon nanocrystals. Nature, 2000, 408, 440-444.	13.7	2,269
2	Correlation between luminescence and structural properties of Si nanocrystals. Journal of Applied Physics, 2000, 87, 1295-1303.	1.1	494
3	Roomâ€temperature electroluminescence from Erâ€doped crystalline Si. Applied Physics Letters, 1994, 64, 2235-2237.	1.5	350
4	Role of the energy transfer in the optical properties of undoped and Er-doped interacting Si nanocrystals. Journal of Applied Physics, 2001, 89, 264-272.	1.1	300
5	Excitation and nonradiative deexcitation processes ofEr3+in crystalline Si. Physical Review B, 1998, 57, 4443-4455.	1.1	267
6	Temperature dependence and quenching processes of the intra-4fluminescence of Er in crystalline Si. Physical Review B, 1994, 49, 16313-16320.	1.1	263
7	Electroluminescence of silicon nanocrystals in MOS structures. Applied Physics A: Materials Science and Processing, 2002, 74, 1-5.	1.1	234
8	The excitation mechanism of rare-earth ions in silicon nanocrystals. Applied Physics A: Materials Science and Processing, 1999, 69, 3-12.	1.1	229
9	The erbiumâ€impurity interaction and its effects on the 1.54 Î¼m luminescence of Er3+in crystalline silicon. Journal of Applied Physics, 1995, 78, 3874-3882.	1.1	187
10	Quantum confinement and recombination dynamics in silicon nanocrystals embedded in Si/SiO2 superlattices. Journal of Applied Physics, 2000, 87, 8165-8173.	1.1	184
11	Modeling and perspectives of the Si nanocrystalsâ€“Er interaction for optical amplification. Physical Review B, 2003, 67, .	1.1	179
12	Mechanism and performance of forward and reverse bias electroluminescence at 1.54 Î¼m from Er-doped Si diodes. Journal of Applied Physics, 1997, 81, 2784-2793.	1.1	164
13	Electroluminescence at 1.54 Î¼m in Er-doped Si nanocluster-based devices. Applied Physics Letters, 2002, 81, 3242-3244.	1.5	164
14	Sensitizing properties of amorphous Si clusters on the 1.54-Î¼m luminescence of Er in Si-rich SiO2. Applied Physics Letters, 2003, 82, 3871-3873.	1.5	156
15	Dynamics of stimulated emission in silicon nanocrystals. Applied Physics Letters, 2003, 82, 4636-4638.	1.5	151
16	Optical activation and excitation mechanisms of Er implanted in Si. Physical Review B, 1993, 48, 11782-11788.	1.1	138
17	Sensitization of Er luminescence by Si nanoclusters. Physical Review B, 2004, 69, .	1.1	131
18	Efficient Luminescence and Energy Transfer in Erbium Silicate Thin Films. Advanced Materials, 2007, 19, 1582-1588.	11.1	124

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19	Er3+â€,ionsâ€“Si nanocrystals interactions and their effects on the luminescence properties. Applied Physics Letters, 2000, 76, 2167-2169.	1.5	123
20	Stimulated emission in plasma-enhanced chemical vapour deposited silicon nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 297-308.	1.3	121
21	High efficiency and fast modulation of Erâ€doped light emitting Si diodes. Applied Physics Letters, 1996, 69, 2077-2079.	1.5	116
22	Nonlinear optical properties of silicon nanocrystals grown by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2002, 91, 4607-4610.	1.1	116
23	Electrical and optical characterization of Erâ€implanted Si: The role of impurities and defects. Journal of Applied Physics, 1993, 74, 4936-4942.	1.1	111
24	Optical and structural properties of Er2O3 films grown by magnetron sputtering. Journal of Applied Physics, 2006, 100, 013502.	1.1	102
25	Excitation and de-excitation properties of silicon quantum dots under electrical pumping. Applied Physics Letters, 2002, 81, 1866-1868.	1.5	96
26	Light absorption in silicon quantum dots embedded in silica. Journal of Applied Physics, 2009, 106, .	1.1	90
27	The effects of oxygen and defects on the deepâ€level properties of Er in crystalline Si. Journal of Applied Physics, 1995, 78, 3867-3873.	1.1	87
28	Defect production and annealing in ion-irradiated Si nanocrystals. Physical Review B, 2002, 65, .	1.1	86
29	Light Emission From Er-Doped Si: Materials Properties, Mechanisms, and Device Performance. MRS Bulletin, 1998, 23, 25-32.	1.7	79
30	Evolution of the local environment around Er upon thermal annealing in Er and O co-implanted Si. Applied Physics Letters, 1997, 70, 1712-1714.	1.5	73
31	Electroluminescence and transport properties in amorphous silicon nanostructures. Nanotechnology, 2006, 17, 1428-1436.	1.3	68
32	Room temperature allâ€silicon photonic crystal nanocavity light emitting diode at subâ€bandgap wavelengths. Laser and Photonics Reviews, 2013, 7, 114-121.	4.4	67
33	Quantum confinement and electroluminescence in ultrathin silicon nanowires fabricated by a maskless etching technique. Nanotechnology, 2012, 23, 075204.	1.3	66
34	Erbium-doped Si nanocrystals: optical properties and electroluminescent devices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 331-340.	1.3	60
35	Linear and nonlinear optical properties of plasma-enhanced chemical-vapour deposition grown silicon nanocrystals. Journal of Modern Optics, 2002, 49, 719-730.	0.6	59
36	Direct evidence of impact excitation and spatial profiling of excited Er in light emitting Si diodes. Applied Physics Letters, 1998, 73, 93-95.	1.5	54

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37	Light amplification in silicon nanocrystals by pump and probe transmission measurements. Journal of Applied Physics, 2004, 96, 5747-5755.	1.1	54
38	Radiative mechanism and surface modification of four visible deep level defect states in ZnO nanorods. Nanoscale, 2016, 8, 995-1006.	2.8	52
39	Electron paramagnetic resonance and photoluminescence study of Er-impurity complexes in Si. Physical Review B, 1999, 59, 2773-2782.	1.1	51
40	Electroluminescence properties of light emitting devices based on silicon nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 395-399.	1.3	50
41	Silicon nanocrystals and Er3+ ions in an optical microcavity. Journal of Applied Physics, 2001, 89, 8354-8356.	1.1	44
42	New Generation of Ultrasensitive Label-Free Optical Si Nanowire-Based Biosensors. ACS Photonics, 2018, 5, 471-479.	3.2	43
43	Mechanism of swelling in low-energy ion-irradiated silicon. Physical Review B, 2001, 65, .	1.1	42
44	Photoluminescence transient study of surface defects in ZnO nanorods grown by chemical bath deposition. Applied Physics Letters, 2015, 106, .	1.5	42
45	Light-emitting silicon nanowires obtained by metal-assisted chemical etching. Semiconductor Science and Technology, 2017, 32, 043004.	1.0	39
46	Microstructural evolution of SiOx films and its effect on the luminescence of Si nanoclusters. Journal of Applied Physics, 2008, 104, 094306.	1.1	38
47	Evidence of energy transfer in an aluminosilicate glass codoped with Si nanoaggregates and Er3+ ions. Journal of Applied Physics, 2004, 96, 3925-3932.	1.1	37
48	Silicon-Based Light-Emitting Devices: Properties and Applications of Crystalline, Amorphous and Er-Doped Nanoclusters. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1596-1606.	1.9	37
49	Photonic-crystal silicon-nanocluster light-emitting device. Applied Physics Letters, 2006, 88, 033501.	1.5	37
50	Evidence for a â€œdarkâ€•state of PbS nanocrystals in a silicate glass. Applied Physics Letters, 2006, 88, 181115.	1.5	36
51	Excitation and non-radiative de-excitation processes in Er-doped Si nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 9-15.	1.7	35
52	Influence of the matrix properties on the performances of Er-doped Si nanoclusters light emitting devices. Journal of Applied Physics, 2010, 107, 054302.	1.1	33
53	Flexible Organic/Inorganic Hybrid Field-Effect Transistors with High Performance and Operational Stability. ACS Applied Materials & Interfaces, 2017, 9, 573-584.	4.0	32
54	Role of the Si excess on the excitation of Er doped SiOx. Applied Physics Letters, 2007, 90, 183102.	1.5	31

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55	Light emitting devices based on silicon nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 181-187.	1.3	31
56	A monolithic silicon detector telescope. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 378, 262-266.	0.7	30
57	Electron paramagnetic resonance of erbium doped silicon. Applied Physics Letters, 1996, 69, 3854-3856.	1.5	30
58	Carrier-induced quenching processes on the erbium luminescence in silicon nanocluster devices. Physical Review B, 2006, 73, .	1.1	30
59	Eu^3+ reduction and efficient light emission in Eu_2O_3 films deposited on Si substrates. Optics Express, 2012, 20, 5501.	1.7	30
60	Materials issues and device performances for light emitting Er-implanted Si. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 386-392.	0.6	29
61	Formation, evolution and photoluminescence properties of Si nanoclusters. Journal of Physics Condensed Matter, 2007, 19, 225003.	0.7	29
62	Enhanced rare earth luminescence in silicon nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 69-70, 335-339.	1.7	28
63	Effect of O:Er concentration ratio on the structural, electrical, and optical properties of Si:Er:O layers grown by molecular beam epitaxy. Journal of Applied Physics, 2000, 88, 4091.	1.1	28
64	Structural and Optical Properties of Silicon Nanocrystals Grown by Plasma-Enhanced Chemical Vapor Deposition. Journal of Nanoscience and Nanotechnology, 2001, 1, 159-168.	0.9	26
65	Transient behavior of the strong violet electroluminescence of Ge-implanted SiO 2 layers. Applied Physics B: Lasers and Optics, 2002, 74, 53-56.	1.1	26
66	Silicon nanowire and carbon nanotube hybrid for room temperature multiwavelength light source. Scientific Reports, 2015, 5, 16753.	1.6	26
67	Optical gain in silicon nanocrystals. Optical Materials, 2001, 17, 41-44.	1.7	25
68	Structure of Er-O complexes in crystalline Si. Physical Review B, 2004, 69, .	1.1	25
69	Correlation between electroluminescence and structural properties of Si nanoclusters. Optical Materials, 2005, 27, 1031-1040.	1.7	24
70	Er site in Er-implanted Si nanoclusters embedded inSiO2. Physical Review B, 2006, 74, .	1.1	24
71	Luminescence properties of Si nanocrystals embedded in optical microcavities. Materials Science and Engineering C, 2002, 19, 377-381.	3.8	23
72	New strategies to improve the luminescence efficiency of Eu ions embedded in Si-based matrices. Journal of Applied Physics, 2013, 113, .	1.1	21

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73	SiOC thin films: an efficient light source and an ideal host matrix for Eu^2+ ions. Optics Express, 2013, 21, 20280.	1.7	20
74	Catalytic role of adsorbates in the photoluminescence emission of Si nanocrystals. Physical Review B, 2008, 78, .	1.1	18
75	Room temperature light emitting silicon diodes fabricated by erbium ion implantation. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 374-377.	0.6	17
76	Chemical composition and local structure of plasma enhanced chemical vapor-deposited Si nanodots and their embedding silica matrix. Applied Physics Letters, 2003, 82, 889-891.	1.5	17
77	New Hybrid Light Harvesting Antenna Based on Silicon Nanowires and Metal Dendrimers. Advanced Optical Materials, 2020, 8, 2001070.	3.6	17
78	Understanding and control of the erbium non-radiative de-excitation processes in silicon. Journal of Luminescence, 1998, 80, 19-28.	1.5	16
79	Size dependence of the luminescence properties in Si nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 69-70, 454-458.	1.7	16
80	The influence of substrate on the properties of Er2O3 films grown by magnetron sputtering. Journal of Luminescence, 2006, 121, 233-237.	1.5	16
81	Temperature dependence and aging effects on silicon nanowires photoluminescence. Optics Express, 2012, 20, 1483.	1.7	16
82	Optical and electrical doping of silicon with holmium. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 497-501.	0.6	15
83	Electroluminescence properties of SiOx layers implanted with rare earth ions. Nuclear Instruments & Methods in Physics Research B, 2004, 216, 222-227.	0.6	15
84	Light absorption enhancement in closely packed Ge quantum dots. Applied Physics Letters, 2013, 102, .	1.5	15
85	MeV ion implantation induced damage in relaxed Si1â^'xGex. Journal of Applied Physics, 1997, 81, 2208-2218.	1.1	14
86	The role of Zn vacancies in UV sensing with ZnO nanorods. Applied Physics Letters, 2016, 109, .	1.5	14
87	Formation of epitaxial Î³-FeSi2 and Î²-FeSi2 layers on (111) Si. Applied Surface Science, 1994, 74, 19-26.	3.1	13
88	Amorphization and recrystallization of ion implanted Si nanocrystals probed through their luminescence properties. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 404-409.	1.3	13
89	Enhancement of Er optical efficiency through bismuth sensitization in yttrium oxide. Applied Physics Letters, 2015, 107, 041908.	1.5	13
90	EPR study of erbium-impurity complexes in silicon. Journal of Luminescence, 1998, 80, 297-301.	1.5	12

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91	Influence of the spatial arrangement on the quantum confinement properties of Si nanocrystals. Optical Materials, 2001, 17, 51-55.	1.7	12
92	Er doped Si nanostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 197-204.	1.7	12
93	Study of the energy transfer mechanism in different glasses co-doped with Si nanoaggregates and Er3+ ions. Optical Materials, 2005, 27, 904-909.	1.7	12
94	Electrical conduction and optical properties of doped silicon-on-insulator photonic crystals. Applied Physics Letters, 2011, 98, 203506.	1.5	12
95	Photonic crystal light emitting diode based on Er and Si nanoclusters co-doped slot waveguide. Applied Physics Letters, 2014, 104, .	1.5	12
96	Large-Area SiC-UV Photodiode for Spectroscopy Portable System. IEEE Sensors Journal, 2019, 19, 2931-2936.	2.4	12
97	Room-temperature luminescence from rare-earth ions implanted into Si nanocrystals. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2000, 80, 719-728.	0.6	11
98	Site of Er ions in Er-implanted silica containing Si nanoclusters. Optical Materials, 2005, 27, 900-903.	1.7	11
99	Revealing the sequential nature of the Si-nanoclusterâ€“Er interaction by variable pulse duration excitation. Physical Review B, 2005, 72, .	1.1	11
100	White light emission from Eu-doped SiOC films. Applied Physics Express, 2014, 7, 012601.	1.1	11
101	Er Luminescence in Si: A Critical Balance between Optical Activity and Pumping Efficiency. Materials Research Society Symposia Proceedings, 1993, 301, 125.	0.1	10
102	EXAFS analysis of Er sites in Erâ€“O and Erâ€“F co-doped crystalline Si. Journal of Luminescence, 1998, 80, 363-367.	1.5	10
103	Oxidation of ion implanted silicon carbide. Materials Science in Semiconductor Processing, 2001, 4, 345-349.	1.9	10
104	X-ray absorption study of light emitting silicon nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 321-325.	1.3	10
105	Thermal evolution and photoluminescence properties of nanometric Si layers. Nanotechnology, 2005, 16, 3012-3016.	1.3	10
106	Time dependence and excitation spectra of the photoluminescence emission at 1.54Î¼m in Si-nanocluster and Er co-doped silica. Optical Materials, 2005, 27, 884-889.	1.7	9
107	Synthesis of crystalline Si quantum dots by millisecond laser irradiation of SiOxNy layers. Journal of Applied Physics, 2010, 107, 023703.	1.1	9
108	Structural and luminescence properties of undoped and Eu-doped SiOC thin films. IOP Conference Series: Materials Science and Engineering, 2014, 56, 012009.	0.3	9

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109	Probe of the Si nanoclusters to Er3+ energy transfer dynamics by double-pulse excitation. Applied Physics Letters, 2005, 87, 061109.	1.5	8
110	Er-based materials for Si microphotonics. Optical Materials, 2009, 31, 1269-1274.	1.7	8
111	Multicolor Depth-Resolved Cathodoluminescence from Eu-Doped SiOC Thin Films. ACS Applied Materials & Interfaces, 2015, 7, 18201-18205.	4.0	8
112	Optical doping of materials by erbium ion implantation. Nuclear Instruments & Methods in Physics Research B, 1996, 116, 77-84.	0.6	7
113	Synthesis and luminescence properties of erbium silicate thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 29-34.	1.7	7
114	Hydrogen induced optically-active defects in silicon photonic nanocavities. Optics Express, 2014, 22, 8843.	1.7	7
115	Visible and infrared emission from Si/Ge nanowires synthesized by metal-assisted wet etching. Nanoscale Research Letters, 2014, 9, 74.	3.1	7
116	Erbium implantation in silicon: from materials properties to light emitting devices. Materials Chemistry and Physics, 1998, 54, 273-279.	2.0	6
117	Erbium Implantation in Silicon: A Way Towards Si-Based Optoelectronics. Materials Research Society Symposia Proceedings, 1993, 316, 397.	0.1	5
118	Erbiumâ€“oxygen interactions in crystalline silicon. Semiconductor Science and Technology, 2011, 26, 055002.	1.0	5
119	A room temperature light source based on silicon nanowires. Thin Solid Films, 2016, 613, 59-63.	0.8	5
120	4H-SiC Detector in High Photons and Ions Irradiation Regime. IEEE Transactions on Electron Devices, 2018, 65, 599-604.	1.6	5
121	Ion beam synthesis of undoped and Er-doped Si nanocrystals. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 140-147.	0.6	4
122	Optical gain in PECVD silicon nanocrystals. , 2002, 4808, 13.		4
123	Light Emitting Devices Based On Silicon Nanocrystals. , 2003, , 29-43.		4
124	Coupling between Ge-nanocrystals and defects in SiO2. Journal of Luminescence, 2006, 121, 409-412.	1.5	4
125	Synthesis and characterization of light emitting Eu2O3 films on Si substrates. Journal of Luminescence, 2012, 132, 3133-3135.	1.5	4
126	Erbium doping of crystalline and amorphous silicon for optoelectronic applications. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1996, 18, 1131-1148.	0.4	3

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127	Ion implantation doping of Si for optoelectronic applications. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 74-80.	0.6	3
128	2 MeV Si ion implantation damage in relaxed Si1â^'xGex. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 165-168.	0.6	3
129	Si:Er:O layers grown by molecular beam epitaxy: structural, electrical and optical properties. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 62-66.	1.7	3
130	Stimulated Emission In Silicon Nanocrystals Gain Measurement And Rate Equation Modelling. , 2003, , 145-164.		3
131	Study of the Si-nanocluster to Er3+ energy transfer dynamics using a double-pulse experiment. Optical Materials, 2006, 28, 815-819.	1.7	3
132	New approaches for enhancing light emission from Er-based materials and devices. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 891-898.	1.3	3
133	Excitation Mechanisms and Light Emitting Device Performances in Er-Doped Crystalline Si. Materials Research Society Symposia Proceedings, 1996, 422, 305.	0.1	2
134	Optical gain in silicon nanocrystals. , 2001, 4293, 162.		2
135	Si Nanocrystals as Sensitizers for Er PL in SiO2. Materials Research Society Symposia Proceedings, 2003, 770, 691.	0.1	2
136	Silicon Nanocrystal Nucleation as a Function of the Annealing Temperature in SiO_x Films. Materials Research Society Symposia Proceedings, 2003, 770, 131.	0.1	2
137	Optical and structural investigation on the energy transfer in a multicomponent glass co-doped with Si nanoaggregates and Er3+ ions. Materials Research Society Symposia Proceedings, 2004, 817, 49.	0.1	2
138	Light emitting devices based on silicon nanoclusters. , 0, , .		2
139	Evaluation of the excess and clustered silicon profiles in a silicon implanted SiO2 layer. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 104-107.	0.6	2
140	Experimental and Theoretical Joint Study on the Electronic and Structural Properties of Silicon Nanocrystals Embedded in SiO₂: active Role of the Interface Region. Materials Research Society Symposia Proceedings, 2003, 770, 611.	0.1	2
141	Oxygen-impurity interactions in crystalline silicon: The cases of aluminum and erbium. Nuclear Instruments & Methods in Physics Research B, 1997, 121, 18-23.	0.6	1
142	Oxidation induced precipitation in Al implanted epitaxial silicon. Journal of Applied Physics, 2000, 88, 3988.	1.1	1
143	Electroluminescent devices based on Er-doped Si nanoclusters. Materials Research Society Symposia Proceedings, 2002, 737, 754.	0.1	1
144	Rare-earth doped Si nanostructures for Microphotonics. Materials Research Society Symposia Proceedings, 2004, 817, 19.	0.1	1

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145	Straactural properties of Si nanocrystals: implications for light emitting devices fabrication. , 2008, , .		1
146	Electrical transport and depletion region in dry-etched Si-based nanostructures. Semiconductor Science and Technology, 2012, 27, 045016.	1.0	1
147	(Invited) Er Doped-Si Nanostructures Coupled with Photonic Crystals for High Enhancement of Light Extraction. ECS Transactions, 2013, 53, 71-80.	0.3	1
148	Impact Excitation And Auger Quenching Processes In Er Doped Light Emitting Si Devices. Materials Research Society Symposia Proceedings, 1997, 486, 127.	0.1	0
149	Electroluminescence of Si Quantum Dots in MOS Structures. Solid State Phenomena, 2002, 82-84, 601-606.	0.3	0
150	Luminescence from Si Nanocrystals and Er³⁺ Ions Embedded in Resonant Cavities. Solid State Phenomena, 2002, 82-84, 617-622.	0.3	0
151	Tuning of the electroluminescence from Si nanocrystals through the control of their structural properties. Materials Research Society Symposia Proceedings, 2002, 737, 291.	0.1	0
152	Optical gain and stimulated emission in silicon nanocrystals. Materials Research Society Symposia Proceedings, 2002, 738, 881.	0.1	0
153	Time-Resolved Gain Dynamics in Silicon Nanocrystals. Materials Research Society Symposia Proceedings, 2003, 770, 341.	0.1	0
154	Coupling and Cooperative Up-conversion Coefficients in Er-doped Si Nanocrystals. Materials Research Society Symposia Proceedings, 2003, 770, 681.	0.1	0
155	Luminescence Properties of a Multi-Component Glass Co-Implanted with Si and Er. Solid State Phenomena, 2004, 99-100, 37-40.	0.3	0
156	Erbium Doped Materials for a Si-Based Microphotonics. Solid State Phenomena, 2007, 131-133, 563-570.	0.3	0
157	Light emitting devices based on Si nanoclusters: the integration with a photonic crystal and electroluminescence properties. Optoelectronics Letters, 2007, 3, 321-325.	0.4	0
158	Influence of stoichiometry on the structural and optical properties of erbium silicate. , 2008, , .		0
159	Electrical and optical properties of ion implanted SOI-based photonic crystals. , 2011, , .		0
160	Microscopic investigations of advanced thin films for photonics. Journal of Physics: Conference Series, 2013, 471, 012004.	0.3	0
161	Room temperature electrically pumped silicon nano-light source at telecommunication wavelengths. Proceedings of SPIE, 2013, , .	0.8	0
162	Silicon photonic crystals: light emission, modulation and detection. , 2014, , .		0

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163	(Invited) Advances in Silicon Nanophotonics. ECS Transactions, 2014, 61, 149-159.	0.3	0
164	New strategies to improve Eu light emission in SI-based matrices. Proceedings of SPIE, 2014, , .	0.8	0
165	Silicon nanowires: a building block for future technologies. , 2021, , .		0
166	Silicon Nanostructures and their Interactions with Erbium Ions. , 2000, , 161-176.		0
167	Materials issues and device performances for light emitting Er-implanted Si. , 1996, , 386-392.		0
168	Nanoscale silicon in photonics and photovoltaics. Series in Materials Science and Engineering, 2017, , 593-616.	0.1	0
169	Structural properties of silicon nanostructures determined by energy-filtered transmission electron microscopy. , 2018, , 429-432.		0
170	Light Emission from Si Nanostructures. Springer Proceedings in Physics, 2008, , 291-300.	0.1	0
171	SILICON NANOCRYSTALS: STRUCTURAL AND OPTICAL PROPERTIES AND DEVICE APPLICATIONS. , 0, , 149-178.		0